

**Amendments to the Specification:**

Please replace the paragraph bridging pages 14 and 15 with the following amended paragraph:

First, a gate line 402 is formed on a substrate 401, and an oxide 403 is formed on the surface of the gate line 402 by an anode-oxidation method if occasion demands. Thereafter, a gate insulating film 404 is formed, a semiconductor channel region 405, a drain region 406 and a source region [[404]] 407 are formed, and then a data line 408 is formed (see Fig. 5(A)). Subsequently, an insulating flattening film 409 of polyimide or the like is formed, and an electrode hole is formed in the insulating flattening film. Thereafter, a transparent conductive film 410 is formed at the front surface, and a photoresist is coated on the front surface (see Fig. 5(B)). The same method as the conventional TFT producing method is used for these processes.